

Silicon NPN Power Transistors

2SD1403

DESCRIPTION

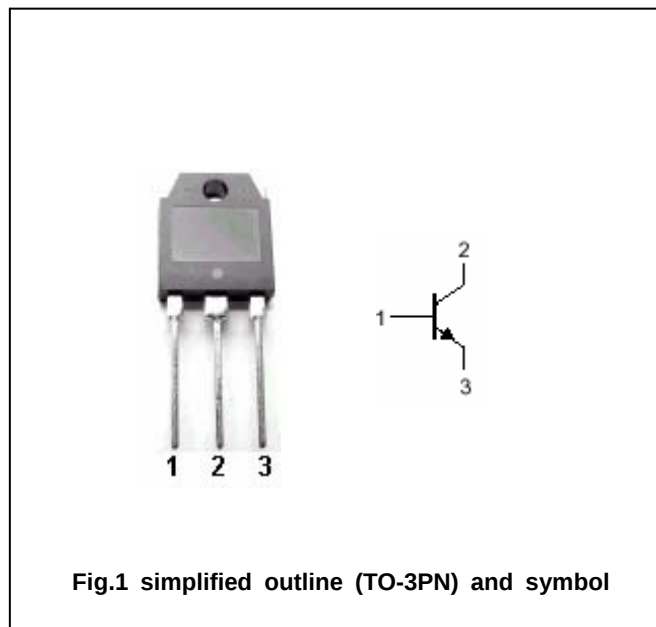
- With TO-3PN package
- High speed switching
- High voltage, high reliability
- Wide area of safe operation

APPLICATIONS

- For CRT horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	120	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			10	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		3		MHz

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Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)